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Analysis of the broad IF-band performance of MgB_2 HEB mixers

Narendra Acharya, Evgenii Novoselov and Sergey Cherednichenko

Abstract— **We present an experimental study of gain and noise bandwidths in superconducting MgB_2 hot-electron bolometer (HEB) THz mixers in a 0.1-20 GHz intermediate frequency range. At an elevated temperature and with a 90 GHz local oscillator, we measure a gain bandwidth of 13-14 GHz, which is the first accurate data for ultrathin MgB_2 films. The output noise spectrum has its maximum in the 100 K-200 K range, depending on the temperature (or the LO power) and the bias point, and its spectrum also confirms the gain bandwidth data obtained with the mixing experiment. Using both the gain and the output noise spectra, we obtain the mixer input noise temperature, which is nearly constant up to 20 GHz. Using the measured data and the HEB mixer theory, we argue that noise bandwidth in the current MgB_2 HEB mixers is ~30 GHz.**

Index Terms— **THz Mixer, HEB mixer, gain bandwidth, noise bandwidth, Intermediate Frequency, magnesium diboride thin films, MgB_2, HPCVD.**

I. Introduction

During the last two decades, superconducting hot-electron bolometer (HEB) mixers have proven to be a successful technology for extremely low-intensity molecular line observations at frequencies above 1 THz [1],[2],[3]. This is because, unlike SIS mixers, the highest operation frequency of HEBs is not limited by the superconducting gap, and, compared to Schottky diode mixers their noise temperature is much lower. The most extensively studied and used HEB mixers are those based on phonon-cooling mechanism of non-equilibrium electrons created by the incident THz radiation [4], [5]. Among them, NbN HEB mixers are the most sensitive heterodyne detectors, with a minimum noise temperature of ~ 500-1000 K [6],[7],[8],[9]. Despite of being state-of-the-art, the gain bandwidth of NbN based phonon-cooled HEB mixers is limited to 2-4 GHz due to about 12 ps of electron-phonon interaction time (τ_{eph}) and 30-40ps of phonon escape time into the substrate [10],[11]. Although for many astronomical tasks such instantaneous bandwidth is sufficient, for observations of broad spectral lines towards the Galactic Center, extragalactic observations, and heterodyne lines surveys a bandwidth in excess of at least 8 GHz is required in order to use a single (or reduced in numbers) LO settings [12], [13].

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All authors work at the Department of Microtechnology and Nanoscience, Chalmers University of Technology, Fysikgrand 3, Gothenburg, Sweden, (e-mail: serguei@chalmers.se) (*Corresponding author Sergey Cherednichenko*).

There have been some efforts to enhance the gain bandwidth of NbN HEBs by initiating a faster phonon escape through an improved film-substrate interface system in various substrate materials [14], [15]. Despite some improvements in the noise temperature, the enhanced IF bandwidth in NbN HEBs has only been reported up to 5-6 GHz. Alternatively, bolometric mixing in chemically doped graphene was recently presented with a demonstrated gain bandwidth of 8 GHz, determined by electron diffusion [16]. However, high sensitivity in graphene hot-electron bolometer mixers, predicted theoretically, is still to be confirmed experimentally.

Due to the advancement in ultrathin superconducting MgB_2 film fabrication technology [17],[18] , in recent years, MgB_2 based HEBs have become a center of interest due to their very fast inelastic electron-phonon interaction (τ_{eph} ~1-2 ps at 40 K) and efficient acoustic matching to both sapphire and SiC substrates [19], [20], [21]. A receiver noise temperature of 1000 K and a noise bandwidth (NBW) of 11 GHz have been reported for MgB_2 HEBs using the Y-factor technique at both 700 GHz and 1.63 THz LO frequencies, with an optimal Local Oscillator power of about 10 μW [22]. With a critical temperature of 30 K, the mixer showed only a minor reduction of sensitivity for operation temperatures up to 20 K.

Earlier gain bandwidth measurements showed that for MgB_2 thin films the gain is almost constant up to 10 GHz (no roll-off), which is a huge improvement compared to any existing state-of-the-art HEBs. Such gain bandwidth (GBW) does not match the 11 GHz NBW [22], because for HEBs an NBW/GBW ratio of ~2 is to be expected [23],[24]. The obvious reason for this discrepancy is the imperfection of the utilized receiver layout, involving the mixer block, the IF amplifier and the interaction between those. In this paper, we study the intrinsic performance of MgB_2 HEB mixers, namely the gain and noise temperature bandwidths, without the influence of the IF chain. In order to be able to do this, we placed the co-planar waveguide (CPW) integrated MgB_2 micro bridges into a cryogenic millimeter wave probe station with an optical signal path and a readout bandwidth of 67 GHz. We measured the gain bandwidth and the output noise spectrum up to 20 GHz, and then calculated the spectrum of the input noise temperature. A similar approach was utilized earlier for the MgB_2 HEB mixer study vs the bias and temperature variations [25]. In order to benchmark the obtained results, we fabricated and tested NbN HEB mixers in the same setup.

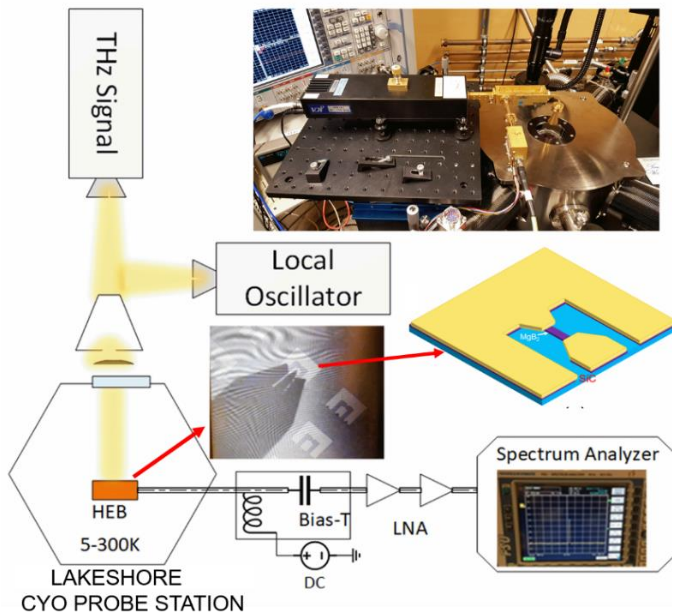

Fig. 1 Experimental set up for both the noise and the gain bandwidths of NbN and MgB_2 HEB mixers. The microwave probe with ground-signal-ground (GSG) contacts and schematic of CPW contact pad along with HEB are shown in the middle. The photograph of the actual set up and the Lakeshore cryo probe station is shown on the top.

II. Device Fabrication and Measurement Setup

A. *HEB Mixer Fabrication*

Our device fabrication process starts with the deposition of ultrathin MgB_2 films (~5-8 nm) on SiC substrates using a custom built hybrid physical chemical vapor deposition (HPCVD) system. Details about our HPCVD system and ultrathin film growth conditions have been described in our previous reports [17],[26] and this process is based on that reported by Zeng *et.al.* [27]. MgB_2 film growth occurred at a substrate temperature of 730 °C and at a chamber pressure of 20 Torr (maintained by the 400 sccm flow of hydrogen (H_2) carrier gas). Magnesium was supplied through the evaporation of Mg slugs placed around the substrate on a resistively heated substrate holder, while boron is provided through the decomposition of diborane gas (5% B_2H_6 in H_2), which is introduced into the vacuum chamber at 2 sccm only during growth. Subsequently, MgB_2 films were transferred to a dc-magnetron sputtering system where plasma cleaning of the film surface (from MgO_x) was carried out, followed by *in situ* sputtering of a 20 nm thick Au film. Similarly, NbN films were deposited on 330 µm thick, C-plane (0001), double- side polished, sapphire substrates by DC reactive magnetron sputtering. The films were deposited from the 2-inch Nb (99.95%) target in an Ar and N_2 environment at 800 °C substrate temperature. For this study, approximately 5 nm thick NbN films were utilized and the thickness was estimated based on the deposition rate.

Both MgB_2 and NbN HEB devices were fabricated by electron beam lithography. First, we defined the coplanar waveguide (CPW) contact pads and alignment marks on the films (Fig. 1). Polymethyl methacrylate (PMMA – 70 nm) on top of copolymer (MMA-470 nm) was utilized as a positive-tone two-layer resist system for electron beam lithography. The subsequent development in mixture of isopropanol and DI water (10:1), electron beam physical vapor deposition (PVD) of Ti-Au-Ti (10 nm-200 nm-40 nm), and lift-off in acetone, leaves the desired patterns on the substrate. The first 10 nm titanium layer promotes the adhesion of Au whereas the final 40 nm layer serves as a mask for gold contact pads later on during the Ar ion milling. The HEB bridges were defined via another electron beam lithography step, with a negative-tone resist (ma-N 2401-100 nm), and developed in tetramethylammonium hydroxide aqueous solution (ma-D 525) followed by rinse in DI water. In the final step, the remaining MgB_2 and NbN were removed by Ar ion milling.

B. *Noise and Gain Characterization*

In order to characterize the gain and the noise spectra, two wafers (one with MgB_2 and another with NbN HEB mixers), were mounted onto the sample holder inside the Lakeshore cryo- probe station (CRX-4K) chamber (Fig.1), which we operated from 40 K (above the T_c of MgB_2) down to 5 K (the base temperature). The measurement set-up diagram, the contact probe, the device layout and the photograph of the Lakeshore probe station are shown in the Fig.1. We have presented data for a 0.5 µm wide × 2 µm long MgB_2 and a 2 µm wide × 0.3 µm long NbN HEBs. In order to be able to contact the samples with the high frequency GSG probe (100µm pitch), the samples have to face upwards, without any Si lens or horn antenna, i.e. with an effective detector area of ~20-30 µm (center contact length of the CPW line (Fig.1)). The sample- to- quartz window distance is ~15 cm, which makes optical coupling quite poor, even for a large focusing lens/mirror above the window. Therefore, in order to make measurements possible, we chose to employ high power WR-10 band sources.

A 90 GHz LO (Omnisys Instruments AB, 20-30 mW output power) and 90-110 GHz Signal (Virginia Diodes Inc., WR10 TxRx modul, ~mW output power) sources were combined with a 10 dB waveguide directional coupler with a 90° waveguide bend and a smooth conical horn facing down towards the window. Two Teflon lenses with focal lengths of 75 mm and 100 mm (not shown in the photo) refocused the beam onto the sample.

Both the DC bias and the IF readout were arranged via a coplanar waveguide probe with the ground-signal-ground

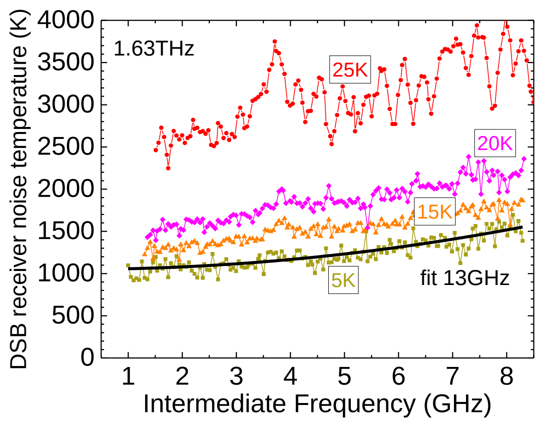

Fig. 2 DSB receiver noise temperature of MgB_2 HEB measured at a 1.63 THz LO, at various temperatures from 5 K to 25 K. The solid curve at 5 K represents the fit for f_N = 13 GHz noise bandwidth.

contact geometry. Low thermal conductivity semirigid coaxial cables lead to a stable sample temperature and microwave readout up to 67 GHz without an appreciable loss. At room temperature, the IF chain consisted of a 40 GHz bias tee (SHF BT45B, SHF AG) and two broadband LNAs (SHF 810, SHF AG and AFS4-0012000 Miteq). The IF chain noise temperature (600-700 K) across the 0.1-20 GHz band (100 MHz step) was measured using Y-factor technique with a microwave noise diode. Both the mixing signal and mixer output noise were recorded using a spectrum analyzer. For the noise measurements, the maximum resolution bandwidth of B=50 MHz was utilized to increase measurements accuracy. The output noise of the HEB mixers was obtained from the following equations:

$$P_N = (T_{out} + T_{LNA})k_B B G_{LNA} \tag{1a}$$
$$P_{ref} = (T_{ref} + T_{LNA})k_B B G_{LNA} \tag{1b}$$

Here, P_N is the measured noise (the HEB and the LNA) with the HEB at the desired operation point; G_{LNA} is the IF chain gain; P_{ref} is the measured noise when the HEB was biased at 100 mV, i.e. in the normal state (see Fig.3a,b); T_{ref} =35 K is the HEB temperature in the normal state (a linear $I(V)$). In a separate set of measurements we observed that the equivalent noise temperature of the HEB bridge at a physical temperature of 35 K (zero bias) is the same as when the HEB is biased at 100 mV being at $<T_c$. It was essential to keep the device at the same physical temperature for both P_N and P_{ref} in order to avoid thermal expansion of the coax cable, which otherwise would lead to standing waves in the T_{out} -spectrum.

As is known [4], the HEB mixer gain (at a particular bias point and LO power) follows the dependence:

$$G(f) = \frac{G(0)}{1+(f/f_0)^2} \tag{2}$$

where G(0) is the gain at zero IF, f is the intermediate frequency, and f_0 is the 3 dB gain roll-off frequency, determined approximately by the electron cooling time τ (this being slightly modified by the bias current effect) as $f_0=1/\tau$. Although the absolute mixer gain could not be measured in our experiments, its IF-dependence was obtained by recording the power of the mixing signal from the LO and the Signal source, $P_{if}(f) \propto G(f)$, when the Signal frequency is tuned from 90 GHz to 110 GHz. Fitting the measured $P_{if}(f)$ with (2) provides the gain bandwidth (f_0) of the mixer.

Samples with CPW contacts did not have antennas, and the coupling of both the LO and the Signal to MgB_2 and NbN micro bridges occurred via the CPW contacts (Fig.1). The coupling factor varied significantly across the frequency tuning range of the Signal source. In order to calibrate for the signal coupling variation, Amplitude Modulation (AM) at 10 kHz was applied to the Signal source, and the coupled power was measured as the HEB direct detection response using a lock-in amplifier. The measured $P_{if}(f)$ data were also corrected for the gain in the IF chain (G_{LNA}).

At 5 K, the photon energy of the 90 GHz LO is much lower than the superconducting energy gaps in both MgB_2 and NbN. Therefore, the samples temperature was set close to T_c in order to reduce the energy gap, hence bringing the devices to the conditions in which the $I(V)$ has to correspond to that where the lowest mixer noise temperatures are typically measured with THz LOs. This approach was frequently utilized for HEB mixer studies, and its validity

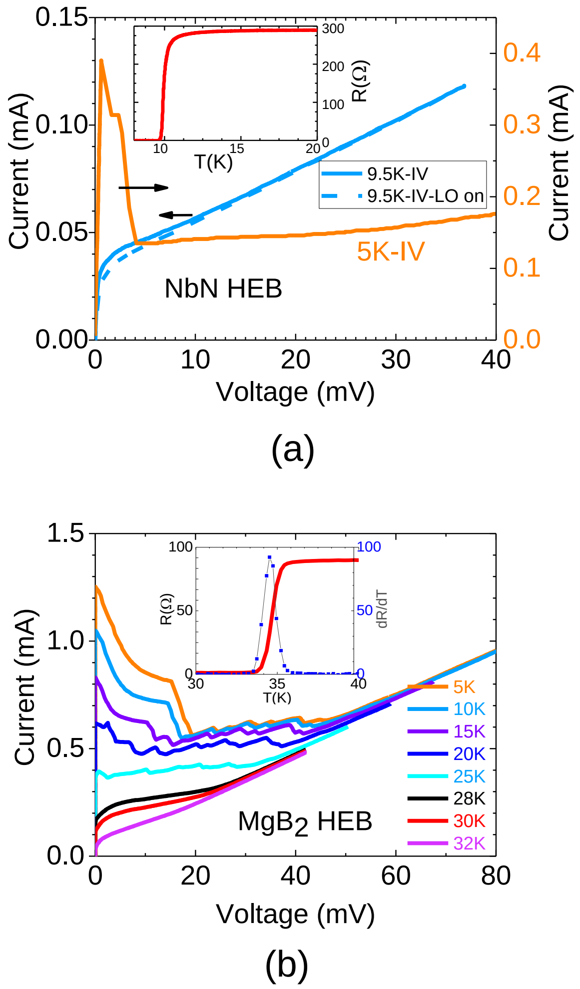

Fig. 3 (a) Current-Voltage, $I(V)$, characteristics of the NbN HEB (2 μm×0.3 μm), at 5 K, and 9.5 K. The blue dash line shows the $I(V)$ at 9.5 K with LO switched on. The inset red curve represents the $R(T)$ of NbN HEB, (b) $I(V)$ characteristics of the MgB_2 HEB (0.5 μm×2 μm) measured at various temperatures from 5 K to 32 K. Inset shows the $R(T)$ and the dR/dT of the same HEB device.

has been confirmed for NbN HEB mixers (see e.g. [14]). For MgB_2 HEBs, the $I(V)$-curves under the optimal power 700 GHz, 1.6 THz, and 2.6 THz LOs have been confirmed to correspond well to the $I(V)$ without an LO, but at a temperature close to T_c [22]. The same being valid also for the output noise [25].

Additionally, a batch of MgB_2 devices was fabricated with THz spiral antennas using MgB_2 films similar to those for the devices described above. Packaged into a mixer block with a Si lens, the noise temperature was measured with Y-factor technique at a 1.63 THz LO at 5 K, 15 K, 20 K, and 25 K operation temperatures (Fig.2) as a reference (see [22]). The measured minimum noise temperature is about 1000 K, i.e. close to that published previously. The fit to the noise temperature spectrum (9) reveals a noise bandwidth of 13 GHz, which is larger than the previously published 11 GHz. We explain this difference by a higher critical temperature and a slightly smaller film thickness for the current batch (32-33 K), which leads to a shorter electron cooling time [21]. An important note: the NBW is the same

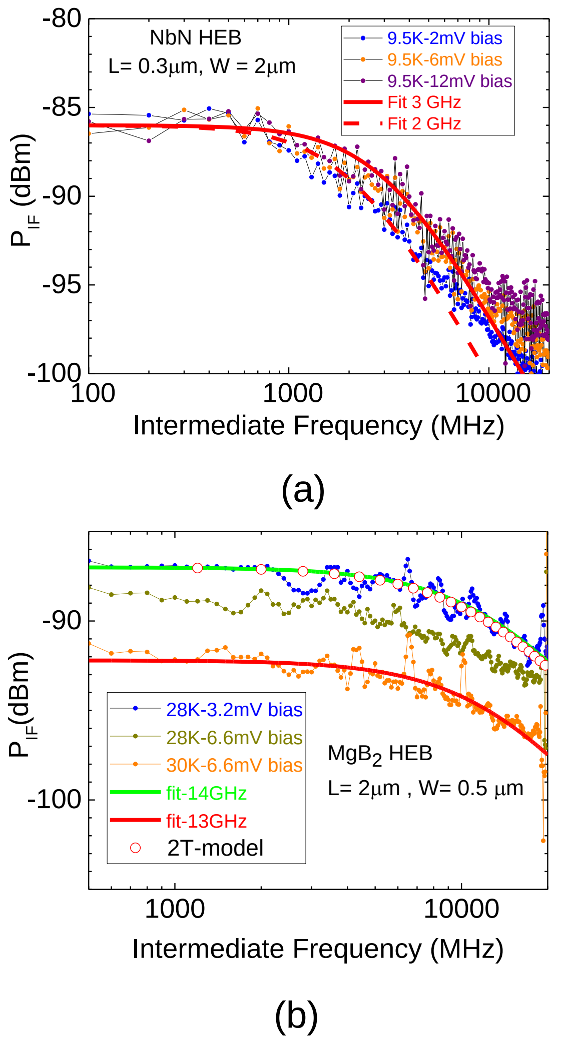

Fig. 4 Mixing signal power versus IF at various bias points, (a) NbN HEB with a 3-dB IF power roll-off (gain bandwidth) at 2-3 GHz and (b) MgB_2 HEB with a gain bandwidth of 14 GHz at 28 K and 13 GHz at 30 K: symbols+lines (measured), solid lines (single-pole Lorentzian fits), open circles (two-temperature modelling).

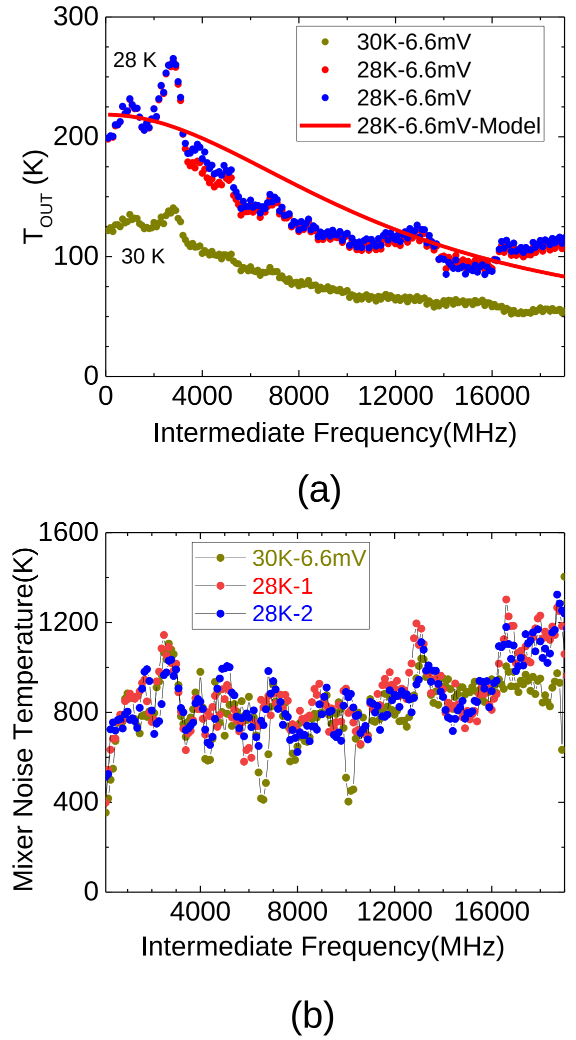

Fig. 5 (a) Output noise of the MgB_2 mixer (T_{out}, see (2)) vs IF, measured at the same bias points as $P_{if}(f)$ in Fig.4(b). The solid line represents the output noise $T_{out}= T_J+ T_{FL}$, calculated using $T_J= T_c$ and T_{FL} according to equation (2). (b) Normalized mixer noise temperature, T_m of the MgB_2 HEB at 30 K and 28 K, obtained as $T_{mix}(f)=[T_{out}(f)/ P_{if}(f)$ +Normalization Factor]. In this case $P_{if}(f)$ was converted to the linear scale.

from 5 K up to at least 25 K. This fact could be used to justify our further experiments at the 28-30 K range using the 90 GHz LO.

III. Results and Discussion

A. I(V) characteristics

I(*V*) characteristics of the NbN HEB at both 5 K and 9.5 K, and that for the MgB_2 HEB at various temperatures from 5 K to 32 K, are shown in Fig. 3(a) and Fig 3(b), respectively. At 5 K, the critical current (I_c) of this MgB_2 HEB sample is 1.25 mA, corresponding to a rather high critical current density of 3×10^7 A/cm^2. Similarly, the normal state resistance of the tested device was 90 Ω (>40 mV), which is consistent with the resistance obtained from the Resistance vs Temperature *R*(*T*) measurement (>35 K). The critical temperatures T_c of both NbN and MgB_2 HEBs were deduced from the *R*(*T*) measurement and come in at 10 K (a typical T_c for thin NbN films) and 33-34 K, respectively (Fig 3 (a), (b), insets). In both samples, narrow transition widths were observed, indicating that the high quality of films was preserved through the HEB fabrication.

B. Gain bandwidth of NbN HEB mixers

In order to benchmark MgB_2 HEB mixers against the well-established technology of NbN HEB mixers, the gain bandwidth of NbN HEBs, integrated with the same CPW contacts as for MgB_2 HEBs, was measured in the same setup. The critical current of the tested NbN sample (w=2 μm × L=0.3 μm) was I_c(5 K)=0.39 mA (Fig. 3(a)). At 9.5 K the *I*(*V*) curve is very similar to that pumped to the optimal performance, with a high frequency LO (f>2Δ) from 4 K [28]. The best fit for the measured (from 100 MHz to 20 GHz) IF response (*Pif*(*f*)) to (2) shows a 3 dB roll-off at 2-3 GHz (Fig.4 (a)), i.e. similar to that previously reported [10], [24].

C. The gain bandwidth and the output noise spectrum of MgB_2 HEB mixers

Based on previous experience [22], [25] , as well as on the sample presented in Fig.2, the best fit to *I*(*V*)-curves optimally pumped with f_{LO}>2Δ *I*(*V*) are those taken in the range 28 K-30 K. Consequently, gain bandwidth was measured at these temperatures, with a small LO power at 90 GHz. The measured gain bandwidth is ~13-14 GHz (Fig.4b), which is the same as for both 28 K and 30 K, and is independent on the bias point along the *I*(*V*).

Measured output noise (Fig.5a) at low IF is in the range 100-200 K, as has been previously reported for both 0.7 THz and 1.63 THz LOs [22]. The noise rolls off as the IF increases, reaching a frequency independent value at IF>10 GHz. Despite the IF chain noise temperature being much higher than the mixer output noise T_{out}, we managed to conduct quite reproducible measurements of $T_{out}(f)$. This fact is confirmed by two curves presented for the 28 K- *I*(*V*) (Fig.5a).

D. Discussion

The output noise in HEBs (as well as in any other thermal detector) is composed of two constituents: the thermal (Johnson) noise T_J, and the temperature fluctuation noise T_{FL}: $T_{out}= T_J+ T_{FL}$. [29]

The thermal fluctuation noise is a strong function of the electron temperature T_e (in superconducting HEBs at the optimal LO and dc drive $T_e \approx T_c$) and $\frac{dR}{dT}$. Following the lumped element HEB model [30],[31]:

$$T_{FL}(T_e) = \frac{4I_0^2\frac{dR}{dT}T_e^2R_LC_0\left(1-C_0I_0^2\right)^2}{(R_0-R_L)^2\left(1+C_0I_0^2\frac{R_0-R_L}{R_0+R_L}\right)^2} \tag{3}$$

$$C_0 \equiv \frac{dR}{dP} = \frac{1}{I_0^2}\times\left[\frac{\frac{dV}{dI}-R_0}{\frac{dV}{dI}+R_0}\right] \tag{4}$$

where the differential resistance $\frac{dV}{dI}$, the dc resistance $R_0=V_0/I_0$, and the bias voltage and current V_0 *and* I_0 can be obtained from the *I*(*V*) characteristics, R_L is the input impedance of the mixer load (the IF amplifier). Equations (3) and (4) are from the lumped HEB model, which is rather simplified and does consider the microscopic physics in superconducting micro bridges. However, being combined with empirically obtained C_0, they have shown to describe well experimental results for low-T_c HEB mixers (Nb, and NbN).

The fluctuation noise spectral dependence is similar to the mixer gain spectrum, i.e.:

$$T_{FL}(f) = \frac{T_{FL}(0)}{1+(f/f_0)^2} \tag{5}$$

The Johnson noise is, to the contrary, frequency independent:

$$T_J= T_c \tag{6}$$

Following [4], the ratio of output noise and gain provides the spectrum of the mixer (input) noise temperature:

$$T_m(f) = \frac{T_{out}(f)}{G(f)} \tag{7}$$

$$T_m(f) = \frac{1}{G(f)}\times\left[\frac{T_{FL}(0)}{1+\left(\frac{f}{f_0}\right)^2}+T_J\right] = \frac{T_{out}(0)}{G(0)}\times\left[1+\frac{T_J}{T_{out}(f)}(f/f_0)^2\right]$$

$$T_m(f) = \frac{T_{out}(0)}{G(0)}\times[1+(f/f_N)^2] \tag{8}$$

Where

$$f_N = f_0\sqrt{\frac{T_{out}(0)}{T_J}} \tag{9}$$

is called the noise bandwidth (the IF at which the mixer input noise temperature increases by a factor of 2 from its value at zero IF). It is clear that the higher the $T_{out}(0)/T_J$ ratio, the larger the f_N vs f_0 becomes. Noise temperature is the main figure of merit of the mixer, and the fact that $f_N > f_0$ is indeed a nice feature in superconducting HEBs where $\frac{T_{out}(0)}{T_J} > 2$ is fairly common.

In practice, HEB mixers operate with (cryogenic) IF amplifiers (LNA), where the system noise temperature (the receiver noise temperature) can be expressed as:

$$T_{rec}(f) = \frac{T_{out}(0)+T_{LNA}}{G(0)}\times[1+(f/f_N^*)^2] \tag{10}$$

Where

$$f_N^* = f_0\sqrt{\frac{T_{out}(0)+T_{LNA}}{T_J+T_{LNA}}} \tag{11}$$

is the system (or the receiver) noise bandwidth. In a terahertz astronomical receiver it is f_N^* which matters, hence the lower the T_{LNA} vs (T_J, T_{out}) the better.

Using device parameters (Fig.3), the measured GBW of 13 GHz and equations (3-6), we calculated the output noise spectrum for the MgB_2 HEB (Fig.5a-solid line). No fitting parameters were utilized in these calculations however, and as can be seen, the calculated curve matches the measured data rather well. Measured $T_{out}(f)$ data can be considered as an independent verification for the mixer gain bandwidth.

Nearly linear scaling of the gain bandwidth with the film thickness, observed for both MBE-grown MgB_2 films on sapphire [21] and HPCVD-grown films on SiC [26], suggests that the process of electron energy relaxation occurs mainly due to inelastic electron-phonon collisions and consequent phonon energy transfer to the substrate [4], [32]:

$$G(f) = 20lg\left[\left|\frac{C_0}{\xi(f,d,Tc)+C_0\frac{R_0-R_L}{R_0+R_L}}\right|\right] \tag{12}$$

where

$$\xi(f,d,Tc) = \frac{(1+j2\pi f\tau_1)(1+j2\pi f\tau_2)}{(1+j2\pi f\tau_3)}$$

$$\tau_{1,2}^{-1} = \frac{\tau_3^{-1}+\tau_{eph}^{-1}}{2}\left[1\pm\sqrt{1-4\frac{\left(\tau_3^{-1}-\tau_{eph}^{-1}\right)^{-2}}{\tau_{eph}\tau_{esc}}}\right]$$

$$\tau_3^{-1} = \tau_{esc}^{-1}+\tau_{eph}^{-1}\frac{c_e}{c_{ph}}$$

Here τ_{eph}, τ_{esc} are electron-phonon interaction time and phonon escape (from the film into the substrate) time. Electron and phonon specific heats c_e and c_{ph} in MgB_2 as well as electron-phonon interaction time and phonon escape (τ_{eph}, τ_{esc}) time have been discussed in previous publications (e.g. [21], [33]). Both mass density and sound velocity in SiC are close to those in sapphire. Therefore, we assume that the phonon escape time from MgB_2 into SiC is the same as into sapphire. With the other relevant parameters in hand (Table I), we simulate the IF spectrum of the conversion gain for the studied MgB_2 HEB mixer (Fig.4b, open circles). The resulting 3 dB roll-off frequency is 13.5 GHz, i.e. very close to the experimental value. For the modeling, the electron temperature T_e is assumed to be equal to T_c [14], [21]. The phonon temperature (T_{ph} =0.8× T_e) was calculated using the system of two heat balance equations: electron-phonon and phonon-substrate [32].

Finally, using the measured gain and the output noise spectra, we can calculate (using (7)) the spectrum of the mixer input noise temperature (Fig.5b). The absolute value of the mixer gain is not known, therefore it is the IF dependence of T_m that we consider. However, we normalized T_m in Fig.5b in order to fit the low IF T_m data obtained with the Y-factor approach (Fig.2). The obtained T_m(20 GHz) is only 20-25 % higher than T_m(1 GHz), which suggests that the noise bandwidth is >20 GHz. On the other hand, using (9), f_0=14 GHz (Fig.4(b)), $T_{out}(0)$ ~150 K (Fig.5(a)), and T_J ~33 K (T_J ~ T_c), we obtain f_N~30 GHz, which should be achievable with a well-designed IF readout.

TABLE I
MgB$_2$ THICKNESS (d), CRITICAL TEMPERATURE (T_C), ELECTRON-PHONON INTERACTION TIME, PHONON ESCAPE TIME, DEBYE TEMPERATURE ,AND SOMMERFELD CONSTANT

d(nm)	Tc(K)	$\tau_{e\text{-}ph}$(ps)	τ_{esc}(ps)	T_D(K)	$\gamma\left(\frac{\text{mJ}}{\text{mol}\cdot\text{K}^2}\right)$
5	34	4.2	5.5	750	3.8
		[21]	[21]	[33]	[33]

MgB$_2$ HEB mixers have much larger T_{out} (100-200 K) compared to NbN HEBs (20-40´K) [34], and the fact that LNA performance is far less critical to MgB$_2$ HEBs compared to NbN HEBs has been previously emphasized. Indeed, with a noise temperature of 3-6 K for cryogenic broadband microwave amplifiers being quite common, the effect of the IF LNA noise on the MgB$_2$ HEB receiver sensitivity is not expected to be significant.

However, so far we have been neglecting the impedance matching and interference between mixer and LNA, the importance of which has been pointed out in previous publications [35],[36]. Therefore, understanding each and every single component in the THz receiver (the mixer, the LNA and the interaction between these) is crucial to obtaining top receiver performance, as is required for astronomy.

IV. Conclusion

In summary, we have characterized MgB$_2$ HEB mixer gain and noise spectra in a broad IF band (from 100 MHz to 20 GHz) utilizing a high quality readout setup at the Lakeshore cryo probe station CRX-4K. We have demonstrated that HEB mixers made from thin (5 nm) MgB$_2$ films have a gain bandwidth of 13-14 GHz, which was also confirmed by the output noise spectrum. This experimental result is in agreement with modeling, which presumes electron cooling via electron-phonon interaction. Mixer noise temperature (excluding the LNA) is nearly constant up to 20 GHz , with noise bandwidth of f_N~30 GHz, calculated based on GBW and output noise. On the other hand, a Si-lens integrated MgB$_2$ HEB mixer shows a minimum noise temperature of 1000 K and a NBW of 13 GHz when a standard IF LNA (2-8 GHz) is used. This, confirms that in order to make use of the full potential of MgB$_2$ HEB mixers, all parts of the receiver (mainly, the mixer and the LNA) have to be carefully designed.

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Narendra Acharya, received his B.Sc. and M.Sc. in physics from Tribhuvan University, Kathmandu, Nepal. In 2017, he received his Ph.D. in physics from Temple University, Philadelphia, USA. His Ph.D. work was focused on growth and characterization of MgB2 thin films for THz detector application and various other superconducting devices such as Josephson junctions and nanowires. He has expertise in thin film growth, device fabrication and low-temperature measurements. Currently, he is a post-doctoral research fellow at Terahertz Millimetre Wave Laboratory at Chalmers University of Technology. His current research is focused on design, fabrication and characterization of MgB2 based THz mixers and superconducting nanowire single-photon detectors (SNSPDs). Research interests include superconducting devices, THz and IR detectors.

Evgenii Novoselov, was born in 1988 in Saint-Petersburg, Russia. He received his B.Sc. and M.Sc. (summa cum laude) in 2009 and 2011, respectively, from The Saint-Petersburg National Research University of Information Technologies, Mechanics and Optics (NRU ITMO). As a part of university studies, Evgenii worked at the research center "Femtosecond optics and femtotechnology" (NRU ITMO) (2007-2011). During that period he participated in several projects on instruments and techniques development for terahertz time-domain spectrography and reflectometry. After completing his master degree, he worked at LLC "TELROS Integration" (Saint-Petersburg, Russia) as a communication systems design engineer (2011-2013).

In 2013, Evgenii joined the Terahertz and Millimetre Wave Laboratory at Chalmers University of Technology, where he successfully defended his PhD thesis «MgB_2 hot-electron bolometer mixers for sub-mm wave astronomy» in 2017. Evgenii is currently with the Microwave Electronics Laboratory working mainly on W-band graphene FET based resistive mixers.

Sergey Cherednichenko, received his Diploma with Honours in Physics in 1993 from Taganrog State Pedagogical Institute, and a Ph.D. in physics in 1999 from Moscow State Pedagogical University.

He is presently working at the Department of Microtechnology and Nanoscience at Chalmers University of Technology (Gothenburg, Sweden).

From 2000-2006 he was involved in the development of terahertz band superconducting mixers for the Herschel Space Observatory; and from 2008 till 2009 in the water vapour radiometer for ALMA. Currently, he is Professor at the department of Microtechnology and Nanoscience at Chalmers University of Technology. His research interests include terahertz heterodyne receivers and mixers, photon detectors; THz antennas and optics; thin superconducting films and their application for THz and photonics; and material properties at THz frequencies.